

with rows of opposing sprocket holes 12 formed on either edge of the above mentioned insulation film, and through holes 14 are disposed two-dimensionally between the rows of sprocket holes 12. Pitch p between through holes 14 is determined by the relationship $m p = n L$ (i.e., n and m are integers, and $n < m$), wherein pitch of the sprocket holes is taken to be L . Through holes 14 are selectively utilized during formation of the desired circuit pattern upon insulation film 10 according to size of the manufactured semiconductor package.--

In the Claims:

Please cancel non-elected Claims 1-4 without prejudice.

5. (amended) A method for manufacture of an insulation film for providing an insulation substrate for carrying a semiconductor chip of a semiconductor package comprising the steps of:

providing an insulation film having two rows of sprocket holes comprising a plurality of sprocket holes formed at a pitch L along both edges of the insulation film; and

forming a two-dimensional plurality of through holes in said insulation film at a pitch p between the rows of sprocket holes.

6. (amended) The method for manufacture of an insulation film according to claim 5 wherein the pitch L and the pitch p satisfy the following equation: $m p = n L$ wherein n and m are integers that satisfy the equation $n < m$.

7. (amended) The method for manufacture of an insulation film according to claim 6 wherein the step of forming the through holes further comprises the steps of:

forming the through holes by collective punching out at the effective sprocket hole formation width of the through holes along the transverse direction of the insulation film in a region of length $n L$ along the length-wise direction of the insulation film;

moving the insulation film a length nL in the length-wise direction by means of the sprocket holes; and
repeating these two steps alternately.

8. (amended) The method for manufacture of an insulation film according to claim 6 wherein the method further comprises a step of forming a two-dimensional plurality of circuit patterns upon the insulation film according to size of the semiconductor package and a for-plating-electricity-supply-use conductor pattern electrically connected with the plurality of circuit patterns.

9. (amended) A method for manufacture of a semiconductor package comprising the steps of: providing an insulation film, forming two rows of sprocket holes comprising a plurality of sprocket holes formed at a pitch L along both edges of the insulation film, forming a two-dimensional plurality of through holes at a pitch p between the rows of sprocket holes, forming a two-dimensional plurality of circuit patterns upon the insulation film according to size of the semiconductor package, forming a for-plating-electricity-supply-use conductor pattern electrically connected with the plurality of circuit patterns having a main line surrounding a perimeter of the plurality of circuit patterns and a sub-line electrically connecting each of the circuit patterns to the main line;

mounting a semiconductor chip within a respective prescribed region of each circuit pattern of the insulation film and electrically connecting the semiconductor chip with the circuit pattern;

performing resin sealing for partitioning off each region enclosed by the main line of the conductor pattern; and

cutting apart into individual semiconductor packages by dicing along the sub-lines of the insulation film.

10. The method for manufacture of a semiconductor package according to claim 9 wherein the method further comprises the step of plating each of the circuit

patterns upon the insulation film using the for-plating-electricity-supply-use conductor pattern.

11. The method for manufacture of a semiconductor package according to claim 9 wherein the dicing step is carried out by use of a dicing blade having a blade trim width wider than the wiring width of the sub-line of the conductor pattern whereby the sub-line is not left behind upon the insulation film.

12. (amended) The method for manufacture of an insulation film according to claim 7 wherein the method further comprises a step of forming a two-dimensional plurality of circuit patterns upon the insulation film according to size of the semiconductor package and a for-plating-electricity-supply-use conductor pattern electrically connected with the plurality of circuit patterns.

13. The method for manufacture of a semiconductor package according to claim 10 wherein the dicing step is carried out by use of a dicing blade having a blade trim width wider than the wiring width of the sub-line of the conductor pattern whereby the sub-line is not left behind upon the insulation film.

Please add the following new claims:

--14. (new) A method of packaging a semiconductor device, comprising the steps of:

providing an insulation film having rows of sprocket holes at a pitch L along the edges of said film and a two-dimensional plurality of through holes in said film between the rows of sprocket holes, said through holes arranged relative to one another at a pitch p ;

mounting a semiconductor chip over a number of said through holes;

sealing said semiconductor chip and a portion of said insulation film in resin; and

cutting said insulation film surrounding said semiconductor chip to release said resin-sealed chip from the remainder of said insulation film.

15. (new) The method of Claim 14, wherein said step of providing an insulation film comprises:

providing an insulation film having rows of sprocket holes at a pitch L along the edges of said film, and a two-dimensional plurality of through holes in said film between the rows of sprocket holes, said through holes arranged relative to one another at a pitch p and continuously along and transversely across said film within circuit pattern regions on said film.

16. (new) The method of Claim 15, wherein said circuit pattern regions are separated by sub-lines of a conductor pattern, and wherein said step of cutting said insulation film comprises cutting said film with a blade having a blade trim width wider than said sub-line whereby said sub-line is not left behind upon the insulation film after said cutting step.

17. (new) The method of Claim 14, wherein said step of providing an insulation film comprises:

providing an insulation film having rows of sprocket holes at a pitch L along the edges of said film, and a two-dimensional plurality of through holes in said film between the rows of sprocket holes, said through holes arranged relative to one another at a pitch p and continuously along and transversely across said film.

18. (new) The method of Claim 14, further comprising the step of depositing solder in selected ones of said number of through holes.

19. (new) The method of Claim 14, further comprising the step of depositing metal in selected ones of said number of through holes.--

In the Claims: